Date: 5/30/2007 Time: 16:30:16

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Inventor Name Search Result

Your Search was:

Last Name = CHOE

First Name = KWANG SW

Application#	Patent#	Status	Date Filed	Title	Inventor Name
09998412	Not Issued	71		Electronic commerce system and operating method thereof	CHOE, KWANG
10334220	6800518	150	12/30/2002	FORMATION OF PATTERNED SILICON-ON-INSULATOR (SOI)/SILICON-ON-NOTHING (SON) COMPOSITE STRUCTURE BY POROUS SI ENGINEERING	CHOE, KWANG SU
10336147	6878611	150	01/02/2003	PATTERNED STRAINED SILICON FOR HIGH PERFORMANCE CIRCUITS	CHOE, KWANG SU
10662028	7125458	150	09/12/2003	FORMATION OF A SILICON GERMANIUM-ON- INSULATOR STRUCTURE BY OXIDATION OF A BURIED POROUS SILICON LAYER	CHOE, KWANG SU
<u>10674647</u> منائح	Not Issued	30	09/30/2003	Thin buried oxides by low-dose oxygen implantation into modified silicon	CHOE, KWANG SU
10674648 Caphan	Not Issued	30	09/30/2003	SOI by oxidation of porous silicon	CHOE, KWANG SU

Inventor Search Completed: No Records to Display.

Last Name First Name Search Another: Inventor KWANG Search

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Inventor Name Search Result

Your Search was:

Last Name = MITCHELL First Name = RYAN ,

Application#	Patent#	Status	Date Filed	Title	Inventor Name
09805380	Not	160	03/13/2001	Method and system for analyzing	MITCHELL, RYAN
	Issued			and planning an inventory	
<u>09805720</u>	Not	161	03/08/2001	Method and system for analyzing	MITCHELL, RYAN
	Issued			and planning an inventory	J.
11038975	Not	30	01/19/2005	Voice-over-internet protocol	MITCHELL RYAN
•	Issued			gateway	J.
60654328	Not	159	02/17/2005	VOIP to wireless gateway	MITCHELL, RYAN
	Issued				<i>y</i> /
11367938	Not	25	03/03/2006	VOIP gateway network	MITCHELL, RYAN
	Issued				JAMES
10674647	Not	30	09/30/2003	Thin buried oxides by low-dose	MITCHELL, RYAN
ا ملک ا	Issued			1 70 1	M.
Mrs				modified silicon	
10710737	7071103	150	07/30/2004	CHEMICAL TREATMENT TO	MITCHELL, RYAN
				RETARD DIFFUSION IN A	M.
				SEMICONDUCTOR	
				OVERLAYER	
10710826	Not	95	08/05/2004	METHOD OF FORMING	MITCHELL, RYAN
	Issued		✓	STRAINED SILICON	M.
				MATERIALS WITH	
				IMPROVED THERMAL	
				CONDUCTIVITY	

Inventor Search Completed: No Records to Display.

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MITCHELL RYAN Search

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PALM INTRANET

Inventor Name Search Result

Your Search was:

Last Name = MAURER

First Name = SIEGFRIED

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Application#	Patent#	Status	Date Filed	Title	Inventor Name			
06272175	4344358	150	06/10/1981	PROCESSING CHAMBER, IN PARTICULAR SMOKING CHAMBER	MAURER, SIEGFRIED			
09526119	Not Issued	168/ 6/P	03/15/2000	Process and circuit arrangement for connecting a mobile radio telephone to a telecommunications network for fixed network telephones	MAURER, SIEGFRIED			
09884670	Not Ussued	161	06/19/2001	Divot reduction in SIMOX layers	MAURER, SIEGFRIED L.			
106041/45	Not Issued	168	06/27/2003	METHOD OF FORMING SILICON-ON-INSULATOR WAFERS HAVING PROCESS RESISTANT APPLICATIONS	MAURER, SIEGFRIED L.			
10604146	Not Issued	71	06/27/2003	METHOD OF FORMING SILICON-ON-INSULATOR WAFERS HAVING PROCESS RESISTANT APPLICATIONS	MAURER, SIEGFRIED L.			
10604149	Not Issued	168/	06/27/2003	Method Of Forming Silicon-On- Insulator Wafers Having Process Resistant Applications	MAURER, SIEGFRIED L.			
10674647	Not Issued	30	09/30/2003	Thin buried oxides by low-dose oxygen implantation into modified silicon	MAURER, SIEGFRIED L.			
10768341	Not Issued		01/30/2004	High electrical quality buried oxide in simox	MAURER, SIEGFRIED L.			
10200822	6784072	150	07/22/2002	CONTROL OF BURIED OXIDE IN SIMOX	MAURER, SIEGFRIED LUTZ			
10896812	Not Issued	71	07/22/2004	Control of buried oxide in SIMOX	MAURER, SIEGFRIED LUTZ			

Inventor Search Completed: No Records to Display.

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Your Search was:

Last Name = SADANA First Name = DEVENDRA



Application#	Patent#	Status	Date Filed	Title	Inventor Name
09205433	6177289	150		LATERAL TRENCH OPTICAL DETECTORS	SADANA, DEVENDRA
09691700	Not Issued	161	10/18/2000	Lateral trench optical detectors	SADANA, DEVENDRA
11679308	Not Issued	30	V	STRAINED SILICON MADE BY PRECIPITATING CARBON FROM Si(1-x-y)GexCy ALLOY	SADANA, DEVENDRA
608) 6050	Not Issued	20	06/23/2006	Buried channel MOSFET using III-V compound semiconductor substrates and high k gate dielectrics	SADANA, DEVENDRA
09031289	6087242	150	1	METHOD TO IMPROVE COMMERCIAL BONDED SOI MATERIAL	SADANA, DEVENDRA KUMAR
08898760	Not Issued	161	07/23/1997	METHOD AND STRUCTURE FOR LATERAL GETTERING OF SILICON-ON-INSULATOR SUBSTRATES	SADANA, DEVENDRA K
60046793	Not Issued	159	02/27/1997	METHOD TO IMPROVE COMMERCIAL BONDED SOI MATERIAL	SADANA, DEVENDRA K
09708337	6404014	1 50		PLANAR AND DENSELY PATTERNED SILICON-ON- INSULATOR STRUCTURE	SADANA, DEVENDRA K.
09757317	6657261	150	 	GROUND-PLANE DEVICE WITH BACK OXIDE TOPOGRAPHY	SADANA, DEVENDRA K.
09791273	6429488	1)50		DENSELY <u>PATTERNED</u> SILICON-ON-INSULATOR (SOI) REGION ON A WAFER	SADANA, DEVENDRA K.
09810236	Not Issued	161/		Body contact in SOI devices by electrically weakening the oxide under the body	SADANA, DEVENDRA K.

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	09861590	6846727	150		PATTERNED SOI BY OXYGEN IMPLANTATION AND ANNEALING	SADANA, DEVENDRA K.
	09861593	6486037	150	05/21/2001	CONTROL OF BURIED OXIDE QUALITY IN LOW DOSE SIMOX	SADANA, DEVENDRA K.
	09861594	6602757)150	05/21/2001	SELF-ADJUSTING THICKNESS UNIFORMITY IN SOI BY HIGH-TEMPERATURE OXIDATION OF SIMOX AND BONDED SOI	SADANA, DEVENDRA K.
	<u>09861596</u>	6541356	150	05/21/2001	THE ULTIMATE SIMOX	SADANA, DEVENDRA K.
Cu.	09874131	Not Issued	161	06/05/2001	Planar substrate with patterned silicon-on- insulator region and self-aligned trench	SADANA, DEVENDRA K.
	09884670	Not Issued	161	06/19/2001	Divot reduction in SIMOX layers	SADANA, DEVENDRA K.
	10055138	6805962	150	01/23/2002	METHOD OF CREATING HIGH-QUALITY RELAXED SIGE-ON-INSULATOR FOR STRAINED SI CMOS APPLICATIONS	SADANA, DEVENDRA K.
	10055139	6495429)150	01/23/2002	CONTROLLING INTERNAL THERMAL OXIDATION AND ELIMINATING DEEP DIVOTS IN SIMOX BY CHLORINE- BASED ANNEALING	SADANA, DEVENDRA K.
	10063994	6642090	150	06/03/2002	FIN FET DEVICES FROM BULK SEMICONDUCTOR AND METHOD FOR FORMING	SADANA, DEVENDRA K.
	10080804	6593205	150	02/21/2002	PATTERNED SOI BY FORMATION AND ANNIHILATION OF BURIED OXIDE REGIONS DURING PROCESSING	SADANA, DEVENDRA K.
		6812114)150	04/10/2002	PATTERNED SOI BY FORMATION AND ANNIHILATION OF BURIED OXIDE REGIONS DURING PROCESSING	SADANA, DEVENDRA K.
	10122009	Not Issued	161		Medium dose simox over a wide BOX thickness range by a multiple implant, multiple anneal process	SADANA, DEVENDRA K.







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	<u>10128794</u>	6743651)150	04/23/2002	METHOD OF FORMING A SIGE-ON-INSULATOR SUBSTRATE USING SEPARATION BY IMPLANTATION OF OXYGEN	SADANA, DEVENDRA K.
	10185580	6756639	1 50		CONTROL OF BURIED OXIDE QUALITY IN LOW DOSE SIMOX	SADANA, DEVENDRA K.
MKE	10196611	6841457)\$0 		USE OF HYDROGEN IMPLANTATION TO IMPROVE MATERIAL PROPERTIES OF SILICON- GERMANIUM-ON- INSULATOR MATERIAL MADE BY THERMAL DIFFUSION	SADANA, DEVENDRA K.
	10280661 (6835983)150		SILICON-ON-INSULATOR (SOI) INTEGRATED CIRCUIT (IC) CHIP WITH THE SILICON LAYERS CONSISTING OF REGIONS OF DIFFERENT THICKNESS	SADANA, DEVENDRA K.
MKF	10300189	<u>6946373</u>	150	11/20/2002	RELAXED, LOW-DEFECT SGOI FOR STRAINED SI CMOS APPLICATIONS	SADANA, DEVENDRA K.
	10318601	<u>6717216</u>	150	1	FIELD EFFECT TRANSISTOR WITH STRESSED CHANNEL AND METHOD FOR MAKING SAME	SADANA, DEVENDRA K.
NKE	10334220	6800518	150		FORMATION OF PATTERNED SILICON-ON-INSULATOR (SOI)/SILICON-ON-NOTHING (SON) COMPOSITE STRUCTURE BY POROUS SI ENGINEERING	SADANA, DEVENDRA K.
	10336147	<u>6878611</u>	150		PATTERNED STRAINED SILICON FOR HIGH PERFORMANCE CIRCUITS	SADANA, DEVENDRA K.
WE	10341819	<u>6717217</u>	150	01/14/2003	ULTIMATE SIMOX	SADANA, DEVENDRA K.
MUR	10448947	6855436	150		FORMATION OF SILICON- GERMANIUM-ON- INSULATOR (SGOI) BY AN INTEGRAL HIGH TEMPERATURE SIMOX-GE INTERDIFFUSION ANNEAL	SADANA, DEVENDRA K.

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Mrk	10448948	7049660	150	05/30/2003	HIGH-QUALITY SGOI BY OXIDATION NEAR THE ALLOY MELTING TEMPERATURE	SADANA, DEVENDRA K.
Wh	10448954	7026249	150	05/30/2003	SIGE LATTICE ENGINEERING USING A COMBINATION OF OXIDATION, THINNING AND EPITAXIAL REGROWTH	SADANA, DEVENDRA K.
my for	10597066	Not Issued	25	07/10/2006	Method of forming thin sgoi- wafers with high relaxation and low stacking fault defect density	SADANA, DEVENDRA K.
,	10604145	Not Issued	168	06/27/2003	METHOD OF FORMING SILICON-ON-INSULATOR WAFERS HAVING PROCESS RESISTANT APPLICATIONS	SADANA, DEVENDRA K.
en de la companya de	10604146	Not Issued	71	06/27/2003	METHOD OF FORMING SILICON-ON-INSULATOR WAFERS HAVING PROCESS RESISTANT APPLICATIONS	SADANA, DEVENDRA K.
	-10604149	Not Issued	168	06/27/2003	Method Of Forming Silicon-On- Insulator Wafers Having Process Resistant Applications	SADANA, DEVENDRA K.
	10604989	6875982	150	X	AN ELECTRON MICROSCOPE MAGNIFICATION STANDARD PROVIDING PRECISE CALIBRATION IN THE MAGNIFICATION RANGE 5000X-2000,000X	SADANA, DEVENDRA K.
MKP	10610612	7169226	150	1	DEFECT REDUCTION BY OXIDATION OF SILICON	SADANA, DEVENDRA K.
MKL	10654231	6803240	150	1 1	METHOD OF MEASURING CRYSTAL DEFECTS IN THIN SI/SIGE BILAYERS	SADANA, DEVENDRA K.
•	10654232 (6989058	50	09/03/2003	USE OF THIN SOI TO INHIBIT RELAXAT <u>ION OF SIGE</u> LAYERS	SADANA, DEVENDRA K.
NKE	10662028	7125458	150		FORMATION OF A SILICON GERMANIUM-ON- INSULATOR STRUCTURE BY OXIDATION OF A BURIED POROUS SILICON LAYER	SADANA, DEVENDRA K.
yk.	10664714	6825102	150		METHOD OF IMPROVING THE QUALITY OF DEFECTIVE SEMICONDUCTOR MATERIAL	SADANA, DEVENDRA K.
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10669727	<u>6884667</u>	150	1	SADANA, DEVENDRA K.
10674647	Not Issued	30	Thin buried oxides by low-dose oxygen implantation into modified silicon	SADANA, DEVENDRA K.
10674648 Cbpw	Not Issued	30 Nun	SOI by oxidation of porous silicon	SADANA, DEVENDRA K.
10685636	Not Issued	121	 Techniques for layer transfer processing	SADANA, DEVENDRA K.
<u>10696601</u>	<u>6861158</u>	150	FORMATION OF SILICON- GERMANIUM-ON- INSULATOR (SGOI) BY AN INTEGRAL HIGH TEMPERATURE SIMOX-GE INTERDIFFUSION ANNEAL	SADANA, DEVENDRA K.

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Inventor Name Search Result.

Your Search was:

Last Name = SADANA First Name = DEVENDRA

Application#	Patent#	Status	Date Filed	Title	Inventor Name
10700085 (7084460) ¹⁵⁰	11/03/2003	METHOD FOR FABRICATING SIGE-ON-INSULATOR (SGOI) AND GE-ON-INSULATOR (GOI) SUBSTRATES	SADANA, DEVENDRA K.
10709114 (6888221	150	04/14/2004	BICMOS TECHNOLOGY ON SIMOX WAFERS	SADANA, DEVENDRA K.
10710826	Not Issued	95	08/05/2004 7	METHOD OF FORMING STRAINED SILICON MATERIALS WITH IMPROVED THERMAL CONDUCTIVITY	SADANA, DEVENDRA K.
10725848	Not Issued	93	12/02/2003	ULTRA-THIN SI MOSFET DEVICE STRUCTURE AND METHOD OF MANUFACTURE	SADANA, DEVENDRA K.
10725849 (7075150	150		ULTRA-THIN SI CHANNEL MOSFET USING A SELF- ALIGNED OXYGEN IMPLANT AND DAMASCENE TECHNIQUE	SADANA, DEVENDRA K.
10751207	Not Issued	161/	01/02/2004	Method of preventing surface roughening during hydrogen prebake of SiGe substrates using chlorine containing gases	SADANA, DEVENDRA K.
10751208	6958286	150		METHOD OF PREVENTING SURFACE ROUGHENING DURING HYDROGEN PREBAKE OF SIGE SUBSTRATES	SADANA, DEVENDRA K.
10768341	Not Issued	161		High electrical quality buried oxide in simox	SADANA, DEVENDRA K.
10818572	Not Issued	161		Method of forming high-quality relaxed SiGe alloy layers on bulk Si substrates	SADANA, DEVENDRA K.

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	10824289	7074686	150		METHOD OF CREATING HIGH-QUALITY RELAXED SIGE-ON-INSULATOR FOR STRAINED SI CMOS APPLICATIONS	SADANA, DEVENDRA K.
	10830347	7087965	150		STRAINED SILICON CMOS ON HYBRID CRYSTAL ORIENTATIONS	SADANA, DEVENDRA K.
	10832215 (6967376	50	11 / / /	DIVOT REDUCTION IN SIMOX LAYERS	SADANA, DEVENDRA K.
	10855915	Not Issued	61		High-quality SGOI by annealing near the alloy melting point	SADANA, DEVENDRA K.
·	10883883	6991998	150		ULTRA-THIN, HIGH QUALITY STRAINED SILICON-ON- INSULATOR FORMED BY ELASTIC STRAIN TRANSFER	SADANA, DEVENDRA K.
/	10883887	7172930	150		STRAINED SILICON-ON- INSULATOR BY ANODIZATION OF A BURIED P+ SILICON GERMANIUM LAYER	SADANA, DEVENDRA K.
	10890765	Not Issued	61	07/14/2004	Ion implantation for suppression of defects in annealed SiGe layers	SADANA, DEVENDRA K.
	10900523	7067371	130		SILICON-ON-INSULATOR (SOI) INTEGRATED CIRCUIT (IC) CHIP WITH THE SILICON LAYERS CONSISTING OF REGIONS OF DIFFERENT THICKNESS	SADANA, DEVENDRA K.
	10902557	Not Issued	93	9	DUAL SIMOX HYBRID ORIENTATION TECHNOLOGY (HOT) SUBSTRATES	SADANA, DEVENDRA K.
	10905477	Not Issued	71		METHOD OF CREATING A Ge- RICH CHANNEL LAYER FOR HIGH-PERFORMANCE CMOS CIRCUITS	SADANA, DEVENDRA K.
	10905595	Not Issued	71	7	LOW CONCENTRATION SIGE BUFFER DURING STRAINED SI GROWTH OF SSGOI MATERIAL FOR DOPANT DIFFUSION CONTROL AND DEFECT REDUCTION	SADANA, DEVENDRA K.
	10923246	7115463)150	08/20/2004	PATTERNING <u>SOI</u> WITH SILICON MASK TO CREATE BOX AT DIFFERENT DEPTHS	SADANA, DEVENDRA K.

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aJAS	10932598	7141115	150	09/02/2004	METHOD OF PRODUCING SILICON-GERMANIUM-ON- INSULATOR MATERIAL USING UNSTRAINED GE- CONTAINING SOURCE LAYERS	SADANA, DEVENDRA K.
MK	10982411	Not Issued	71	11/05/2004	Use of hydrogen implantation to improve material properties of silicon-germanium-on-insulator material made by thermal diffusion	SADANA, DEVENDRA K.
MKs MKs	10984212	Not Issued	41	11/09/2004	Formation of silicon-germanium- on-insulator (SGOI) by an integral high temperature SIMOX-Ge interdiffusion anneal	SADANA, DEVENDRA K.
	10992150	7141457	150	11/18/2004	METHOD TO FORM SICONTAINING SOLAND UNDERLYING SUBSTRATE WITH DIFFERENT ORIENTATIONS	SADANA, DEVENDRA K.
WIKE	10993270	Not Issued	61	11/19/2004	Patterned SOI by oxygen implantation and annealing	SADANA, DEVENDRA K.
MKE	11029921	Not Issued	41	01/05/2005	High-quality SGOI by oxidation near the alloy melting temperature	SADANA, DEVENDRA K.
	11031165	Not Issued	30		Quasi-hydrophobic Si-Si wafer bonding using hydrophilic Si surfaces and dissolution of interfacial bonding oxide	SADANA, DEVENDRA K.
alls	11039602	7084050	150		FORMATION OF SILICON- GERMANIUM-ON-INSULATOR (SGOI) BY AN INTEGRAL HIGH TEMPERATURE SIMOX- GE INTERDIFFUSION ANNEAL	SADANA, DEVENDRA K.
	11116053	Not Issued	30		Field effect transistor with mixed- crystal-orientation channel and source/drain regions	SADANA, DEVENDRA K.
	<u>11164345</u>	Not Issued	30	ック	HYBRID CRYSTALLOGRAPHIC SURFACE ORIENTATION SUBSTRATE HAVING ONE OR MORE SOI REGIONS AND/OR BULK SEMICONDUCTOR REGIONS	SADANA, DEVENDRA K.
ME	11208359	Not Issued	71		Relaxed, low-defect SGOI for strained Si CMOS applications	SADANA, DEVENDRA K.

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	11259654	Not Issued	71	_	Method for tuning epitaxial growth by interfacial doping and structure including same	SADANA, DEVENDRA K.
VIKT	<u>11268096</u> .	Not Issued	71	II - {	Use of thin SOI to inhibit relaxation of SiGe layers	SADANA, DEVENDRA K.
NKE NKE	11293774	Not Issued	30		Ultra-thin, high quality strained silicon-on-insulator formed by elastic strain transfer	SADANA, DEVENDRA K.
`\	11327675	Not Issued	25	01/06/2006	High k gate stack on III-V compound semiconductors	SADANA, DEVENDRA K.
.146	11332564	Not Issued	71		Strained semiconductor-on- insulator (sSOI) by a simox method	SADANA, DEVENDRA K.
MKE	11333074	Not Issued	30	01/17/2006	Structure and method to form semiconductor-on-pores (SOP) for high device performance and low manufacturing cost	SADANA, DEVENDRA K.
	11384718	Not Issued	30		Structure and method for controlling the behavior of dislocations in strained semiconductor layers	SADANA, DEVENDRA K.
	11401672	Not Issued	30		CMOS process with Si gates for nFETs and SiGe gates for pFETs	SADANA, DEVENDRA K.
	11402177	Not Issued	30		Control of poly-Si depletion in CMOS via gas phase doping	SADANA, DEVENDRA K.
	11417846	Not Issued	30		Ion implantation combined with in situ or ex situ heat treatment for improved field effect transistors	SADANA, DEVENDRA K.
Vogoz		Not Issued	30		Ultra-thin Si channel MOSFET using a self-aligned oxygen implant and damascene technique	SADANA, DEVENDRA K.
Rilleg	11481525	Not Issued	41		Method for fabricating SiGe-on- insulator (SGOI) and Ge-on- insulator (GOI) substrates	SADANA, DEVENDRA K.
	11492271	Not Issued	30		Strained silicon CMOS on hybrid crystal orientations	SADANA, DEVENDRA K.
MK	11619040	Not Issued	30	01/02/2007	DEFECT REDUCTION BY OXIDATION OF SILICON	SADANA, DEVENDRA K.
	11620224	Not Issued	25	X	Structures containing electrodeposited germanium and methods for their fabrication	SADANA, DEVENDRA K.
WKT	11620663	Not Issued	30		STRAINED SILICON-ON- INSULATOR BY ANODIZATION OF A BURIED p+ SILICON GERMANIUM	SADANA, DEVENDRA K.
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11678338	Not Issued			SADANA, DEVENDRA K.
06210488	4371774	150		SADANA, DEVENDRA K.

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Last Name = SADANA First Name = DEVENDRA

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Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>07487501</u>	Not Issued	166	03/02/1990	CONTROLLED SILICON DOPING OF III-V COMPOUNDS BY THERMAL OXIDATION OF SILICON CAPPING LAYER	SADANA, DEVENDRA K.
07655512	5183767	250	02/14/1991 %	METHOD FOR INTERNAL GETTERING OF OXYGEN IN III-V COMPOUND SEMICONDUCTORS	SADANA, DEVENDRA K.
07754276 (5188978)250	08/30/1991	CONTROLLED SILICON DOPING OF III-V COMPOUNDS BY THERMAL OXIDATION OF SILICON CAPPING LAYER	SADANA, DEVENDRA K.
07913560	5242859	250		HIGHLY DOPED SEMICONDUCTOR MATERIAL AND METHOD OF FABRICATION THEREOF	SADANA, DEVENDRA K.
07945858	5272373	250	09/16/1992 •∕A	INTERNAL GETTERING OF OXYGEN IN III-V COMPOUND SEMICONDUCTORS	SADANA, DEVENDRA K.
08575421	Not Issued	161	12/20/1995	METHOD AND STRUCTURE FOR LATERAL GETTERING OF SILICON-ON-INSULATOR SUBSTRATES	SADANA, DEVENDRA K.
08678442	5767549) 150	07/03/1996	SOI CMOS STRUCTURE	SADANA, DEVENDRA K.
09193606	6214694			PROCESS OF MAKING DENSELY PATTERNED SILICON-ON-INSULATOR (SOI) REGION ON A WAFER	SADANA, DEVENDRA K.
<u>09227696</u> (6255145	150	01/08/1999	PROCESS FOR MANUFACTURING PATTERNED SILICON-ON-	SADANA, DEVENDRA K.

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					INSULATOR LAYERS WITH SELF- ALIGNED TRENCHES AND RESULTING PRODUCT	
	09250895	6180486	150	02/16/1999	PROCESS OF FABRICATING PLANAR AND DENSELY PATTERNED SILICON-ON- INSULATOR STRUCTURE	SADANA, DEVENDRA K.
	<u>09427256</u>	6426252	1 50	10/25/1999) ,	SILICON-ON-INSULATOR VERTICAL ARRAY DRAM CELL WITH SELF-ALIGNED BURIED STRAP	SADANA, DEVENDRA K.
	09427257 (6566177	150	10/25/1999	SILICON-ON-INSULATOR VERTICAL ARRAY DEVICE TRENCH CAPACITOR DRAM	SADANA, DEVENDRA K.
N	60032331	Not Issued	159	12/03/1996	SILICON-ON-INSULATOR SUBSTRATES USING LOW DOSE IMPLANTATION	SADANA, DEVENDRA Ķ.
	60039989	Not Issued	159	03/05/1997	METHOD OF FORMING BURIED OXIDE LAYERS IN SILICON	SADANA, DEVENDRA K.
	09531628	6222253	150	03/21/2000	Buried Oxide Layer In Silicon	SADANA, DEVENDRA KUMAR
	09567095	6300218	150	05/08/2000	Method for patterning a buried oxide thickness for a separation by implanted oxygen (simox) process	SADANA, DEVENDRA KUMAR 7
	09788979 (6432754	150		RECESS ETCH AND EPITAXY	SADANA, DEVENDRA KUMAR
	09975435	6756257)150	II I	PATTERNED SOI REGIONS ON SEMICONDUCTOR CHIPS	SADANA, DEVENDRA KUMAR
ysm	10200822	6784072	150	07/22/2002	CONTROL OF BURIED OXIDE IN SIMOX	SADANA, DEVENDRA KUMAR
SM	10896812	Not Issued	71	07/22/2004	Control of buried oxide in SIMOX	SADANA, DEVENDRA KUMAR
all!	10990300	Not Issued	41	11/15/2004	Ultrathin buried insulators in Si or Si-containing material	SADANA, DEVENDRA KUMAR
	11031142	Not Issued	41	4	defect-density changed orientation	SADANA, DEVENDRA KUMAR

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11046912	Not Issued	93	01/31/2005	STRUCTURE AND METHOD OF INTEGRATING COMPOUND AND ELEMENTAL SEMICONDUCTORS FOR HIGH-PERFORMACE CMOS	SADANA, DEVENDRA KUMAR
08961131	6043166)150	10/30/1997	SILICON-ON-INSULATOR SUBSTRATES USING LOW DOSE IMPLANTATION	SADANA, DEVENDRA KUMAR
08995585 (5930643)150	12/22/1997	DEFECT INDUCED BURIED OXIDE (DIBOX) FOR THROUGHPUT SOI	SADANA, DEVENDRA KUMAR
09034445	6090689)50	03/04/1998	METHOD OF FORMING BURIED OXIDE LAYERS IN SILICON	SADANA, DEVENDRA KUMAR
09264973	6259137)150	03/09/1999	DEFECT INDUCED BURIED OXIDE (DIBOX) FOR THROUGHPUT SOI	SADANA, DEVENDRA KUMAR
09312217	6204546	150		SILICON-ON-INSULATOR SUBSTRATES USING LOW DOSE IMPLANTATION	SADANA, DEVENDRA KUMAR
09356295	6333532)50	07/16/1999	PATTERNED SOI REGIONS IN SEMICONDUCTOR CHIPS	SADANA, DEVENDRA KUMAR

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Appli	cation#	Patent#	Status	Date Filed	Title	Inventor Name
0748	<u>85016</u>	4975079	250		CONNECTOR ASSEMBLY FOR CHIP TESTING	FOGEL, KEITH
107	10826	Not Issued	95	08/05/2004	METHOD OF FORMING STRAINED SILICON MATERIALS WITH IMPROVED THERMAL CONDUCTIVITY	FOGEL, KEITH
1092	28473	7172431	150	08/27/2004	ELECTRICAL CONNECTOR DESIGN AND CONTACT GEOMETRY AND METHOD OF USE THEREOF AND METHODS OF FABRICATION THEREOF	FOGEL, KEITH
0908	81342	6525551	150		PROBE STRUCTURES FOR TESTING ELECTRICAL INTERCONNECTIONS TO INTEGRATED CIRCUIT ELECTRONIC DEVICES	FOGEL, KEITH EDWARD
1033	<u>36147</u>	<u>6878611</u>	150	L	PATTERNED STRAINED SILICON FOR HIGH PERFORMANCE CIRCUITS	FOGEL, KEITH E
6002	26088	Not Issued	159		WAFER SCALE HIGH DENSITY PROBE ASSEMBLY	FOGEL, KEITH E
0986	61590	6846727)50		PATTERNED SOI BY OXYGEN IMPLANTATION AND ANNEALING	FOGEL, KEITH E.
0986	61596 (6541356	150	05/21/2001	THE ULTIMATE SIMOX	FOGEL, KEITH E.
		6805962)		METHOD OF CREATING HIGH- QUALITY RELAXED SIGE-ON- INSULATOR FOR STRAINED SI CMOS APPLICATIONS	FOGEL, KEITH E. ? 5.Ge
1019	96611 (6841457	150		USE OF HYDROGEN IMPLANTATION TO IMPROVE MATERIAL PROPERTIES OF	FOGEL, KEITH E.

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				SILICON-GERMANIUM-ON- INSULATOR MATERIAL MADE BY THERMAL DIFFUSION	
10300189	6946373	150	11/20/2002	RELAXED, LOW-DEFECT SGOI FOR STRAINED SI CMOS 1,000 APPLICATIONS	FOGEL, KEITH E. M S. & OT
10334220	6800518	150	12/30/2002	FORMATION OF PATTERNED SILICON-ON-INSULATOR (SOI)/SILICON-ON-NOTHING (SON) COMPOSITE STRUCTURE BY POROUS SI ENGINEERING	FOGEL, KEITH E.
<u>10341819</u> (6717217) 50	01/14/2003	ULTIMATE SIMOX	FOGEL, KEITH E.
10448947	685'5436)150	05/30/2003	FORMATION OF SILICON- GERMANIUM-ON-INSULATOR (SGOI) BY AN INTEGRAL HIGH TEMPERATURE SIMOX-GE INTERDIFFUSION ANNEAL	FOGEL, KEITH E.
10448948 (7049660)150	05/30/2003	HIGH-QUALITY <u>SGOI BY</u> OXIDATION NEAR THE ALLOY MELTING TEMPERATURE	FOGEL, KEITH E.
10448954 (7026249)150	05/30/2003 1	SIGE LATTICE ENGINEERING USING A COMBINATION OF OXIDATION, THINNING AND EPITAXIAL REGROWTH	FOGEL, KEITH E.
10531494	Not Issued	30		Land grid array fabrication using elastomer core and conducting metal shell or mesh	FOGEL, KEITH E.
10610612	7169226	150	07/01/2003	DEFECT REDUCTION BY OXIDATION OF SILICON	FOGEL, KEITH E.
10654231	6803240	150	∥ \.	METHOD OF MEASURING CRYSTAL DEFECTS IN THIN SI/SIGE BILAYERS	FOGEL, KEITH E.
10654232	6989058	150	09/03/2003	USE OF THIN SOI TO INHIBIT RELAXATION OF SIGE LAYERS	FOGEL, KEITH E.
10662028	7125458	150	09/12/2003	FORMATION OF A SILICON GERMANIUM-ON-INSULATOR STRUCTURE BY OXIDATION OF A BURIED POROUS SILICON LAYER	FOGEL, KEITH E.
<u>10664714</u>	6825102	150		METHOD OF IMPROVING THE QUALITY OF DEFECTIVE SEMICONDUCTOR MATERIAL	FOGEL, KEITH E.

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	10674647 Hus	Not Issued	30		Thin buried oxides by low-dose oxygen implantation into modified silicon	FOGEL, KEITH E.
1	10674648 Open	Not Issued	30	09/30/2003	SOI by oxidation of porous silicon	FOGEL, KEITH E.
	10696601	6861158)150	10/29/2003	FORMATION OF SILICON- GERMANIUM-ON-INSULATOR (SGOI) BY AN INTEGRAL HIGH TEMPERATURE SIMOX-GE INTERDIFFUSION ANNEAL	FOGEL, KEITH E.
	10715288	7137827	150	11/17/2003	INTERPOSER WITH ELECTRICAL CONTACT BUTTON AND METHOD	FOGEL, KEITH E.
	10768341	Not Issued	161	01/30/2004	High electrical quality buried oxide in simox	FOGEL, KEITH E.
	10815103	Not Issued	41	$ \setminus \wedge $	Interconnections for flip-chip using lead-free solders and having reaction barrier layers	FOGEL, KEITH E.
-	10818572	Not Issued	161		Method of forming high-quality relaxed SiGe alloy layers on bulk Si substrates	FOGEL, KEITH E.
	10824289	7074686	150		METHOD OF CREATING HIGH- QUALITY RELAXED SIGE-ON- INSULATOR FOR STRAINED SI CMOS APPLICATIONS	FOGEL, KEITH E.
1	(0855915	Not Issued	61		High-quality SGOI by annealing near the alloy melting point	FOGEL, KEITH E.
	10883883	6991998	1 50		ULTRA-THIN, HIGH QUALITY STRAINED SILICON-ON- INSULATOR FORMED BY ELASTIC STRAIN TRANSFER	FOGEL, KEITH E.
	10883887	7172930)150	. .	STRAINED SILICON-ON- INSULATOR BY ANODIZATION OF A BURIED P+ SILICON GERMANIUM LAYER	FOGEL, KEITH E.
	10890765	Not Issued	61	07/14/2004	Ion implantation for suppression of defects in annealed SiGe layers	FOGEL, KEITH E.
	10932598 (7141115)150		METHOD OF PRODUCING SILICON-GERMANIUM-ON- INSULATOR MATERIAL USING UNSTRAINED GE- CONTAINING SOURCE LAYERS	FOGEL, KEITH E.





all by	10982411	Not Issued	71	11/05/2004	Use of hydrogen implantation to improve material properties of silicon-germanium-on-insulator material made by thermal diffusion	FOGEL, KEITH E.
ply .	10984212	Not Issued	41		Formation of silicon-germanium- on-insulator (SGOI) by an integral high temperature SIMOX-Ge interdiffusion anneal	FOGEL, KEITH E.
M. Or	10993270	Not Issued	61		Patterned SOI by oxygen implantation and annealing	FOGEL, KEITH E.
Pallor	11029921	Not Issued	41		High-quality SGOI by oxidation near the alloy melting temperature	FOGEL, KEITH E.
	11039602 (7084050) 50	01/19/2005	FORMATION OF SILICON- GERMANIUM-ON-INSULATOR (SGOI) BY AN INTEGRAL HIGH TEMPERATURE SIMOX-GE INTERDIFFUSION ANNEAL	FOGEL, KEITH E.
molin	11208359	Not Issued	71	08/19/2005	Relaxed, low-defect SGOI for strained Si CMOS applications	FOGEL, KEITH E.
`	11220324	Not Issued	30		Interposer with electrical contact button and method	FOGEL, KEITH E.
Ylong	11268096	Not Issued	71		Use of thin SOI to inhibit relaxation of SiGe layers	FOGEL, KEITH E.
Pag	11293774	Not Issued	30	ï	Ultra-thin, high quality strained silicon-on-insulator formed by elastic strain transfer	FOGEL, KEITH E.
pul ch	11332564	Not Issued	71	01/13/2006	Strained semiconductor-on- insulator (sSOI) by a simox method	FOGEL, KEITH E.
Organia de la companya de la company	11333074	Not Issued	30	*	Structure and method to form semiconductor-on-pores (SOP) for high device performance and low manufacturing cost	FOGEL, KEITH E.
	11406122	Not Issued	30	04/18/2006	Laser processing method for trench-edge-defect-free solid phase epitaxy in confined geometrics	FOGEL, KEITH E.
	11424642	Not Issued		4	THERMALLY CONDUCTIVE COMPOSITE INTERFACE, COOLED ELECTRONIC ASSEMBLIES EMPLOYING THE SAME, AND METHODS OF FABRICATION THEREOF	FOGEL, KEITH E.
	11561273	Not Issued	25	\ \ \	INTERPOSER WITH ELECTRICAL CONTACT BUTTON AND METHOD	FOGEL, KEITH E.



(11619040	Not	30	01/02/2007	DEFECT REDUCTION BY	FOGEL, KEITH E.
		Issued			OXIDATION OF SILICON	

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I	Application#	Patent#	Status	Date Filed	Title	Inventor Name
	11620663	Not Issued	30		STRAINED SILICON-ON- INSULATOR BY ANODIZATION OF A BURIED p+ SILICON GERMANIUM LAYER	FOGEL, KEITH E.
	11678338	Not Issued	25	02/23/2007	LOW- <u>TEM</u> PERATURE ELECTRICALLY ACTIVATED GATE ELECTRODE AND METHOD OF FABRICATING SAME	FOGEL, KEITH E.
	60421480	Not Issued	159	10/24/2002	Land grid array fabrication using elastomer core and conducting metal shell or mesh	FOGEL, KEITH E.
	07963346	5371654	150		THREE DIMENSIONAL HIGH PERFORMANCE INTERCONNECTION PACKAGE	FOGEL, KEITH E.
	08055485	<u>5635846</u>	150	×	TEST PROBE HAVING ELONGATED CONDUCTOR EMBEDDED IN AN ELASTOMERIC MATERIAL WHICH IS MOUNTED ON A SPACE TRANSFORMER	FOGEL, KEITH E.
	08224383	Not Issued	166		INTEGRAL RIGID CHIP TEST PROBE	FOGEL, KEITH E.
	08300620	5531022	150	09/02/1994 >	METHOD OF FORMING A THREE DIMENSIONAL HIGH PERFORMANCE INTERCONNECTION PACKAGE	FOGEL, KEITH E.
	08323554	5541567	150		COAXIAL VIAS IN AN ELECTRONIC SUBSTRATE	FOGEL, KEITH E.
	08324053	Not Issued	161	10/17/1994 ·•	METHODS OF FABRICATION OF COAXIAL VIAS AND	FOGEL, KEITH E.

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				MAGNETIC DEVICES	
08425543	Not Issued	161		HIGH DENSITY INTEGRAL TEST PROBE AND FABRICATION METHOD	FOGEL, KEITH E.
08425639	Not Issued	161	04/20/1995	HIGH TEMPERATURE CHIP TEST PROBE	FOGEL, KEITH E.
08527733	5810607	150	09/13/1995 V	INTERCONNECTOR WITH CONTACT PADS HAVING ENHANCED DURABILITY	FOGEL, KEITH E.
08614417	5811982	150	03/12/1996 V	HIGH DENSITY CANTILEVERED PROBE FOR ELECTRONIC DEVICES	FOGEL, KEITH E.
08614456	Not Issued	160	03/12/1996	HIGH DENSITY TEST PROBE WITH RIGID SURFACE STRUCTURE	FOGEL, KEITH E.
08641667	5785538	150	05/01/1996 X)	HIGH DENSITY TEST PROBE WITH RIGID SURFACE STRUCTURE	FOGEL, KEITH E.
08739343	6286208	150	10/28/1996	INTERCONNECTOR WITH CONTACT PADS HAVING ENHANCED DURABILITY	FOGEL, KEITH E.
08744903	<u>5838160</u>	150	11/08/1996 Q	INTEGRAL RIGID CHIP TEST PROBE	FOGEL, KEITH E.
08752469	6054651	150	X	FOAMED ELASTOMERS FOR WAFER PROBING APPLICATIONS AND INTERPOSER CONNECTORS	FOGEL, KEITH E.
<u>08754869</u>	<u>5821763</u>	150	11/22/1996	TEST PROBE FOR HIGH DENSITY INTEGRATED CIRCUITS METHODS OF FABRICATION THEREOF AND METHODS OF USE THEREOF	FOGEL, KEITH E.
0 8756830	Not Issued	167	11/20/1996	HIGH DENSITY INTEGRAL TEST PROBE	FOGEL, KEITH E.
08756831	Not Issued	161	11/20/1996	HIGH TEMPERATURE CHIP TEST PROBE	FOGEL, KEITH E.
09076267	6078500	150		PLUGGABLE CHIP SCALE PACKAGE	FOGEL, KEITH E.
09162717	Not Issued	169	09/29/1998	PLATED PROBE STRUCTURE	FOGEL, KEITH E.
09164470	6295729	150		ANGLED FLYING LEAD WIRE BONDING PROCESS	FOGEL, KEITH E.
09251988	Not Issued	41		STRUCTURAL DESIGN AND PROCESSES TO CONTROL PROBE POSITION ACCURACY	FOGEL, KEITH E.

•				•	
				IN A WAFER TEST PROBE ASSEMBLY	
<u>-60020000</u>	Not Issued	159	06/21/1996	FOAMED ELASTOMERS FOR WAFER PROBING APPLICATIONS AND INTERPOSER CONNECTORS	FOGEL, KEITH E.
60026050	Not Issued	159	09/13/1996	CHIP PROBE STRUCTURE HAVING A PLURALITY OF DISCRETE INSULATED PROBE TIPS PROJECTING FROM A SUPPORT SURFACE	FOGEL, KEITH E.
60026112	Not Issued	159	09/13/1996	INTEGRATED COMPLIANT PROBE FOR WAFER LEVEL TEST AND BURNIN	FOGEL, KEITH E.
<u>6</u> 0047556	Not Issued	159	05/22/1997	PROBE STRUCTURE WITH ENHANCED DURABILITY	FOGEL, KEITH E.
60047558	Not Issued	159	05/22/1997	PLUGGABLE CHIP SCALE PACKAGE	FOGEL, KEITH E.
60060877	Not Issued	159	10/02/1997	ANGLED FLYING LEAD WIRE BONDING PROCESS	FOGEL, KEITH E.
60060878	Not Issued	159	10/02/1997	PLATED PROBE STRUCTURE	FOGEL, KEITH E.
09165832	6891360	150	10/02/1998 X	PLATED PROBE STRUCTURE	FOGEL, KEITH EDWARD
09254768	6528984	150	03/11/1999 ` X	INTEGRATED COMPLIANT PROBE FOR WAFER LEVEL TEST AND BURN-IN	FOGEL, KEITH EDWARD
09884848	Not Issued	161		Deformable coated wick liquid spilled material transfer	FOGEL, KEITH EDWARD
<u>09871536</u>	6526655	150		ANGLED FLYING LEAD WIRE BONDING PROCESS	FOGEL, KEITH EDWARD
09886960	6523255	150	06/21/2001 ^	PROCESS AND STRUCTURE TO REPAIR DAMAGED PROBES MOUNTED ON A SPACE TRANSFORMER	FOGEL, KEITH EDWARD
<u>09921867</u>	Not Issued	61		High density integrated circuit apparatus, test probe and methods of use thereof	FOGEL, KEITH EDWARD
09928285	6722032	150	08/10/2001 XI	A METHOD OF FORMING A STURCTURE FOR ELECTRONIC DEVICES CONTACT LOCATIONS	FOGEL, KEITH EDWARD
09972622	Not Issued	161/		HIGH DENSITY INTEGRAL TEST PROBE APPARATUS FOR TESTING ELECTRONIC	FOGEL, KEITH EDWARD

				DEVICES	
10066171	Not Issued	41		Probe structure having a plurality of discrete insulated probe tips projecting from a support surface, apparatus for use thereof and methods of fabrication thereof	FOGEL, KEITH EDWARD
10145661	Not Issued	71	05/14/2002 **X	STRUCTURAL DESIGN AND PROCESSES TO CONTROL PROBE POSITION ACCURACY IN A WAFER TEST PROBE ASSEMBLY	FOGEL, KEITH EDWARD
10202069	Not Issued	41	07/23/2002	Probe structure having a plurality of discrete insulated probe tips projecting from a support surface, apparatus for use thereof and methods of fabrication thereof	FOGEL, KEITH EDWARD
10341794	Not Issued	161	01/14/2003	Compliant interposer assembly for wafer test and "burn-in" operations	
10342167	6708403	150	01/14/2003	ANGLED FLYING LEAD WIRE BONDING PROCESS	FOGEL, KEITH EDWARD
<u>10408200</u>	Not Issued	41		High density integrated circuit apparatus, test probe and methods of use thereof	FOGEL, KEITH EDWARD
10685636	Not Issued	121	10/15/2003	Techniques for layer transfer processing	FOGEL, KEITH EDWARD
10736890	Not Issued	41	12/16/2003	Angled flying lead wire bonding process	FOGEL, KEITH EDWARD
10742685	6880245	150	. ^	A METHOD FOR FABRICATING A STRUCTURE FOR MAKING CONTACT WITH AN IC DEVICE	FOGEL, KEITH EDWARD
11031142	Not Issued	41		Method for fabricating low-defect- density changed orientation Si	FOGEL, KEITH EDWARD

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Application#	Patent#	Status	Date Filed	Title	Inventor Name
11101309	Not Issued	71	04/07/2005	A METHOD FOR FABRICATING A STRUCTURE FOR MAKING CONTACT WITH A DEVICE	FOGEL, KEITH EDWARD
11142646	Not Issued	71	06/01/2005 A		FOGEL, KEITH EDWARD
08783738	5898991	150		METHODS OF FABRICATION OF COAXIAL VIAS AND MAGNETIC DEVICES	FOGEL, KEITH EDWARD
08872519	6334247	150	06/11/1997 >	HIGH DENSITY INTEGRATED CIRCUIT APPARATUS, TEST PROBE AND METHODS OF USE THEREOF	FOGEL, KEITH EDWARD
08946141	5914614	150	10/07/1997 %	HIGH DENSITY CANTILEVERED PROBE FOR ELECTRONIC DEVICES	FOGEL, KEITH EDWARD
09078174	6062879	150	05/13/1998 プ	HIGH DENSITY TEST PROBE WITH RIGID SURFACE STRUCTURE	FOGEL, KEITH EDWARD
09088394	6300780	150	06/01/1998 \square	HIGH DENSITY INTEGRATED CIRCUIT APPARATUS, TEST PROBE AND METHODS OF USE THEREOF	FOGEL, KEITH EDWARD
09162474	6104201	150	þ	METHOD AND APPARATUS FOR PASSIVE CHARACTERIZATION OF SEMICONDUCTOR SUBSTRATES SUBJECTED TO HIGH ENERGY (MEV) ION IMPLEMENTATION USING HIGH-INJECTION SURFACE PHOTOVOLTAGE	FOGEL, KEITH EDWARD
<u>09198179</u>	6332270	150		1	FOGEL, KEITH EDWARD

				PROBE	
09208529	6329827	150	12/09/1998 \	HIGH DENSITY CANTILEVERED PROBE FOR ELECTRONIC DEVICES	FOGEL, KEITH EDWARD
09251864	6206273	150	02/17/1999 •{}	STRUCTURES AND PROCESSES TO CREATE A DESIRED PROBETIP CONTACT GEOMETRY ON A WAFER TEST PROBE	FOGEL, KEITH EDWARD
09254769	Not Issued	98	03/11/1999	WAFER SCALE HIGH DENSITY PROBE ASSEMBLY, APPARATUS FOR USE THEREOF AND METHODS OF FABRICATION THEREOF	FOGEL, KEITH EDWARD
<u>09254798</u>	6452406	150	03/11/1999 \ ⁄o	PROBE STRUCTURE HAVING A PLURALITY OF DISCRETE INSULATED PROBE TIPS	FOGEL, KEITH EDWARD
09382834	Not Issued	40		HIGH DENSITY INTEGRATED CIRCUIT APPARATUS, TEST PROBE AND METHODS OF USE THEREOF	FOGEL, KEITH EDWARD

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Inventor Name	City	State/Country				
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MITCHELL, RYAN M.	CLINTONDALE	NEW YORK				
SADANA, DEVENDRA K.	PLEASANTVILLE	NEW YORK				
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